

Nikolay I Gorbachuk

List of Publications by Year in descending order

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papers

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#	ARTICLE	IF	CITATIONS
1	IMPEDANCE SPECTROSCOPY OF POLYCRYSTALLINE TIN DIOXIDE FILMS. <i>Pribory I Metody Izmerenij</i> , 2016, 7, 312-321.	0.3	8
2	Influence of Defects Introduced by Irradiation with 4-9 MeV Helium Ions on Impedance of Silicon Diodes. <i>Acta Physica Polonica A</i> , 2015, 128, 891-894.	0.5	0
3	Current-Voltage Characteristic Features of Diodes Irradiated with 170-MeV Xenon Ions. <i>Acta Physica Polonica A</i> , 2013, 123, 926-928.	0.5	0
4	Impedance of Single-Walled Carbon Nanotube Fibers. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2012, 20, 434-438.	2.1	4
5	Impedance of Si/SiO ₂ composites in the vicinity of the percolation threshold. <i>Physics of the Solid State</i> , 2011, 53, 462-466.	0.6	3
6	Optical spectroscopy of the surface of nanoporous diamond films. <i>Journal of Applied Spectroscopy</i> , 2011, 78, 563-571.	0.7	6
7	Effects of Fluences of Irradiation with 107 MeV Krypton Ions on the Recovery Charge of Silicon p ⁺ -n-Diodes. <i>Acta Physica Polonica A</i> , 2011, 120, 111-114.	0.5	4
8	AC-Conductivity of Thin Polycrystalline Tin Dioxide Films. <i>Acta Physica Polonica A</i> , 2011, 119, 146-147.	0.5	0
9	The dependence of the conductivity of SiO ₂ -Fe ₂ O ₃ film composites on air humidity. <i>Russian Journal of Physical Chemistry A</i> , 2010, 84, 684-688.	0.6	2
10	Influence of radiation defects on electrical losses in silicon diodes irradiated with electrons. <i>Semiconductors</i> , 2010, 44, 380-384.	0.5	2
11	Equivalent circuit of silicon diodes subjected to high-fluence electron irradiation. <i>Technical Physics</i> , 2010, 55, 1463-1471.	0.7	9
12	Impedance and barrier capacitance of silicon diodes implanted with high-energy Xe ions. <i>Microelectronics Reliability</i> , 2010, 50, 813-820.	1.7	9
13	Kinetics of reverse resistance recovery of silicon diodes: The role of the distance the metallurgical p+n-junction-defect layer formed by 250MeV krypton implantation. <i>Physica B: Condensed Matter</i> , 2009, 404, 4667-4670.	2.7	6
14	Electrical properties of silicon diodes with p+n junctions irradiated with ¹⁹⁷ Au+ ²⁶ swift heavy ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008, 266, 5007-5012.	1.4	10
15	Formation of coloring complexes in glass colored with cerium and titanium oxides. <i>Glass and Ceramics (English Translation of Steklo I Keramika)</i> , 2007, 64, 346-348.	0.6	11
16	Magnetoresistive effect and impedance spectroscopy of Co-implanted polyimide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 1545-1549.	1.8	7
17	Negative capacitance (impedance of the inductive type) of silicon p+n junctions irradiated with fast electrons. <i>Semiconductors</i> , 2006, 40, 803-807.	0.5	14
18	Nanostructuring of crystalline grains of natural diamond using ionizing radiation. <i>Semiconductors</i> , 2005, 39, 894-897.	0.5	7

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19	Electrical Conductivity of Composite Materials Based on Fine-Particle Silicon near the Metal-Insulator Transition. <i>Inorganic Materials</i> , 2004, 40, 1133-1138.	0.8	7
20	X-ray-Induced Paramagnetic Centers in SiO ₂ Xerogels. <i>Inorganic Materials</i> , 2001, 37, 482-486.	0.8	0
21	Effect of the Moisture Content on the Electrical Conductivity of SiO ₂ /LiCl Xerogels. <i>Glass Physics and Chemistry</i> , 2001, 27, 520-526.	0.7	4